

FORM PTO-1449  
(REV. 7-80)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
51889/4 USAPPLICATION NO.  
10/733,612

## INFORMATION DISCLOSURE CITATION

Title: SRAM Cell



APPLICANT - Douglas R. Hackler, Sr. et al.

FILING DATE-  
December 11, 2003

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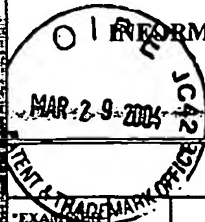
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Docket Number (Optional)

51889/4

Application Number

10/733,612

Applicant(s)

Douglas R. Hackler, Sr. et al.

Filing Date

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Group Art Unit

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**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TH	A1	2003/0058001	03/27/03	Boerstler et al.	326	113	09/27/01
	A2	2002/0180486	12/05/02	Yamashita et al.	326	113	06/25/02
	A3	2002/0084803	07/04/02	Mathew et al.	326	113	12/29/00
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TH	A11	6,188,243	02/13/01	Liu et al.	326	81	06/09/99

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)


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**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

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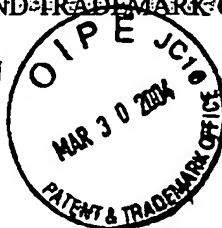
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		DOCUMENT NUMBER	PUBLICA- TION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	20							
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